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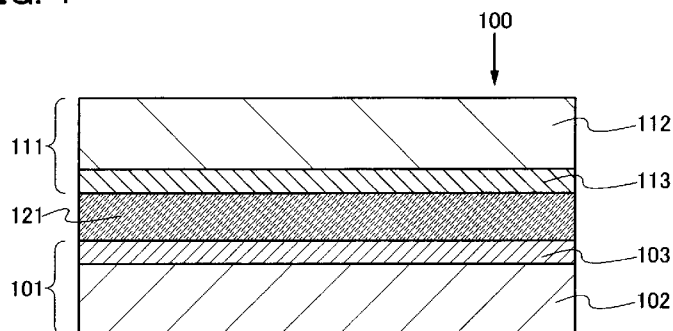
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(54) Title: POWER STORAGE DEVICE AND METHOD FOR MANUFACTURING THE POWER STORAGE DEVICE

FIG. 1



(57) Abstract: To provide a power storage device having a solid electrolyte, in which a charge-discharge capacity can be increased, and a method for manufacturing the power storage device. The power storage device includes a positive electrode, a negative electrode, and an electrolyte provided between the positive electrode and the negative electrode, and the electrolyte includes an ion-conductive high molecular compound, an inorganic oxide, and a lithium salt, and the inorganic oxide is included in the electrolyte at more than 30 wt % and 50 wt % or less to the total of the ion-conductive high molecular compound and the inorganic oxide.